

METHOD OF MAKING A MICROMECHANICAL DEVICE

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Abstract of the Disclosure

A method of making a micromechanical device including forming a dielectric layer over a sacrificial layer, wherein the dielectric layer includes silicon, oxygen and nitrogen. In one embodiment, the dielectric layer is silicon oxynitride formed using plasma enhanced chemical vapor deposition (PECVD). Silicon oxynitride can easily be formed as a low stress material, unlike silicon dioxide, and does not have a large charge trap density like silicon nitride.

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